

BD242/A/B/C

Medium Power Linear and Switching Applications

• Complement to BD241/A/B/C respectively



1.Base 2.Collector 3.Emitter

Rev. A, February 2000

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|--|------------|-------|
| V _{CEO} | Collector-Emitter Voltage | | |
| | : BD242 | - 45 | V |
| | : BD242A | - 60 | V |
| | : BD242B | - 80 | V |
| | : BD242C | - 100 | V |
| V _{CER} | Collector-Emitter Voltage | | |
| | : BD242 | - 55 | V |
| | : BD242A | - 70 | V |
| | : BD242B | - 90 | V |
| | : BD242C | - 115 | V |
| V _{EBO} | Emitter-Base Voltage | - 5 | V |
| I _C | Collector Current (DC) | - 3 | Α |
| I _{CP} | *Collector Current (Pulse) | - 5 | Α |
| I _B | Base Current | - 1 | Α |
| P _C | Collector Dissipation (T _C =25°C) | 40 | W |
| TJ | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | - 65 ~ 150 | °C |

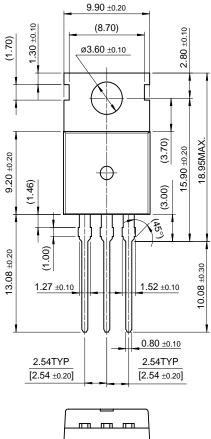
$\textbf{Electrical Characteristics} \ \, \textbf{T}_{\text{C}} = 25 ^{\circ} \text{C unless otherwise noted}$

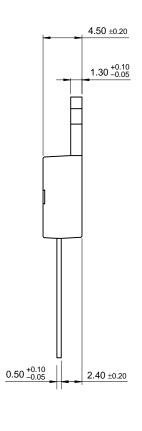
| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|------------------------|--|--------------------------------|-------|------|-------|-------|
| V _{CEO} (sus) | * Collector-Emitter Sustaining Voltage | | | | | |
| | : BD242 | $I_C = -30 \text{mA}, I_B = 0$ | - 45 | | | V |
| | : BD242A | | - 60 | | | V |
| | : BD242B | | - 80 | | | V |
| | : BD242C | | - 100 | | | V |
| I _{CEO} | Collector Cut-off Current : BD242/A | $V_{CE} = -30V, I_{B} = 0$ | | | - 0.3 | mA |
| | : BD242B/C | $V_{CE} = -60V, I_{B} = 0$ | | | - 0.3 | mA |
| I _{CES} | Collector Cut-off Current : BD242 | $V_{CE} = -45V, V_{BE} = 0$ | | | - 0.2 | mA |
| | : BD242A | $V_{CE} = -60V, V_{BE} = 0$ | | | - 0.2 | mA |
| | : BD242B | $V_{CE} = -80V, V_{BE} = 0$ | | | - 0.2 | mA |
| | : BD242C | $V_{CE} = -100V, V_{BE} = 0$ | | | - 0.2 | mA |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = -5V, I_{C} = 0$ | | | - 1 | mA |
| h _{FE} | * DC Current Gain | $V_{CE} = -4V, I_{C} = -1A$ | 25 | | | |
| | | $V_{CE} = -4V, I_{C} = -3A$ | 10 | | | |
| V _{CE} (sat) | * Collector-Emitter Saturation Voltage | $I_C = -3A$, $I_B = -0.6A$ | | | - 1.2 | V |
| V _{BE} (on) | * Base-Emitter ON Voltage | $V_{CE} = -4V, I_{C} = -3A$ | | _ | - 1.8 | V |
| Pulse Test: PW=3 | | • | | • | | • |

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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